



600 V POWER MOSFETs

SiHG22N60S-E3 / SiHG47N60S-E3

MOSFETs

PRODUCT OVERVIEW



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Vishay is adding to its Super Junction power MOSFET family with new n-channel devices in the TO-247 package, featuring ultra-low maximum on-resistance and low gate charge for an improved figure of merit (FOM).

Features:

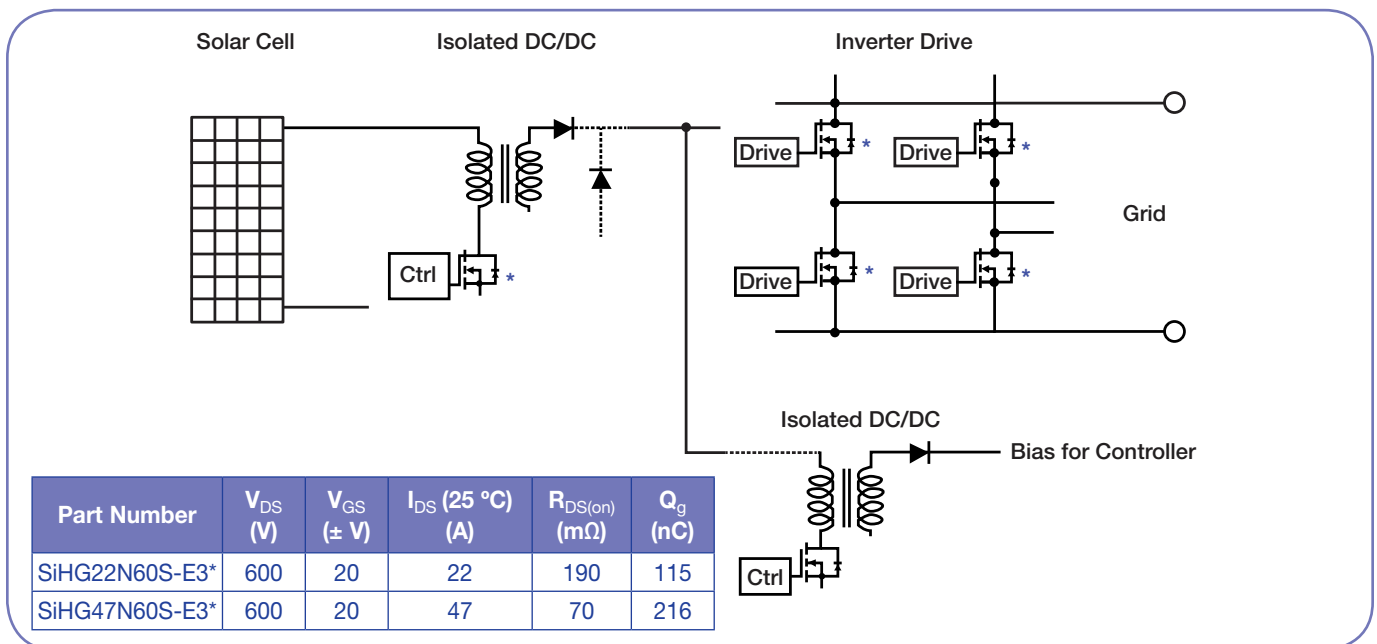
- High E_{AR} capability
- Improved $R_{ON} \times Q_g$ figure of merit (FOM)
 - 18.81 $\Omega \cdot nC$ (SiHG22N60S-E3)
 - SiHP22N60S-E3, SiHF22N60S-E3, and SiHB22N60S-E3 also available
 - 15.12 $\Omega \cdot nC$ (SiHG47N60S-E3)
- Ultra-low $R_{DS(on)}$
- Ultra-low gate charge (Q_g)
- 100 % avalanche tested
- dV/dt ruggedness
- Compliant to RoHS Directive 2002/95/EC

Applications

- PFC power supply stages
- Hard switching topologies
- Solar inverters
- UPS
- Motor control
- Lighting
- Server telecom

These devices are produced using Vishay Super Junction technology, which has been tailored to minimize on-state resistance and withstand high energy pulses in the avalanche and commutation modes.

Solar Cell and Inverter Block Diagram

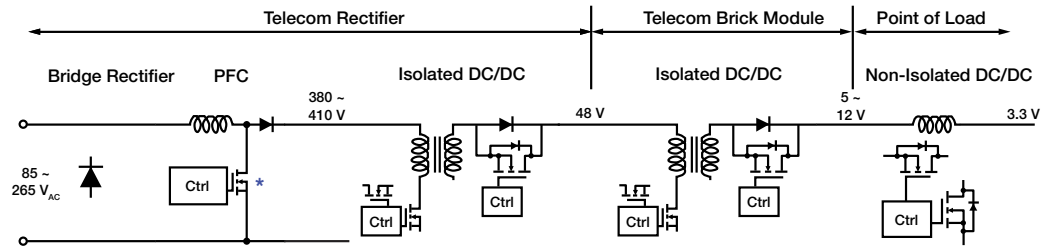


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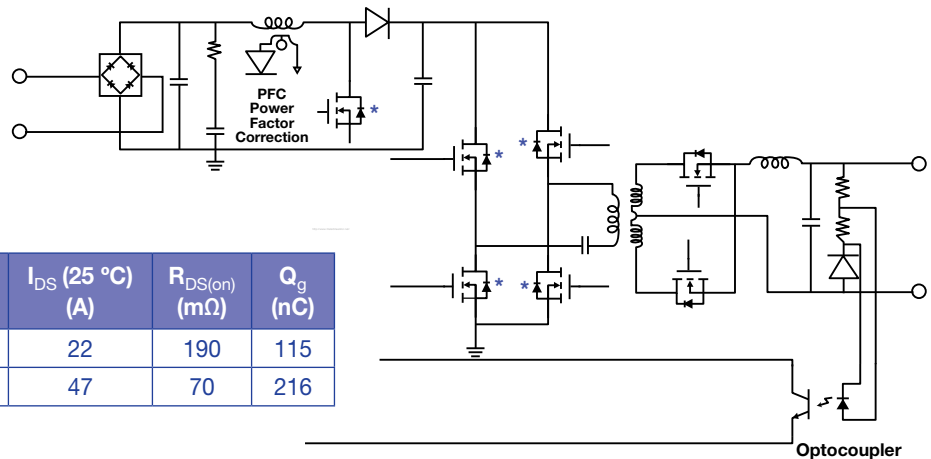


Telecom Power Supply Block Diagram



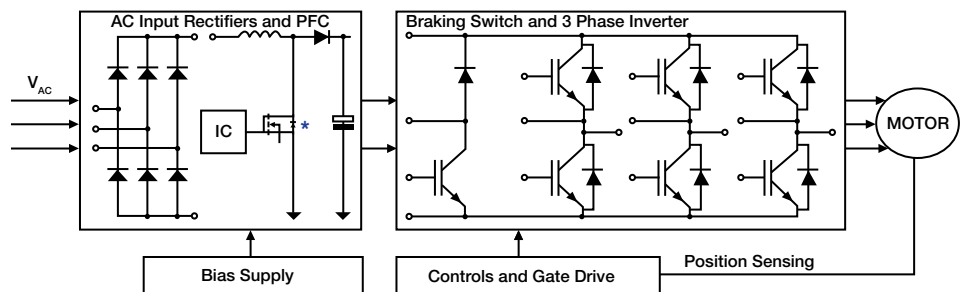
| Part Number | V _{DS} (V) | V _{GS} (± V) | I _{DS} (25 °C) (A) | R _{DS(on)} (mΩ) | Q _g (nC) |
|----------------|---------------------|-----------------------|-----------------------------|--------------------------|---------------------|
| SiHG22N60S-E3* | 600 | 20 | 22 | 190 | 115 |
| SiHG47N60S-E3* | 600 | 20 | 47 | 70 | 216 |

Server Power Supply Block Diagram



| Part Number | V _{DS} (V) | V _{GS} (± V) | I _{DS} (25 °C) (A) | R _{DS(on)} (mΩ) | Q _g (nC) |
|----------------|---------------------|-----------------------|-----------------------------|--------------------------|---------------------|
| SiHG22N60S-E3* | 600 | 20 | 22 | 190 | 115 |
| SiHG47N60S-E3* | 600 | 20 | 47 | 70 | 216 |

Motor Control Power Supply Block Diagram



| Part Number | V _{DS} (V) | V _{GS} (± V) | I _{DS} (25 °C) (A) | R _{DS(on)} (mΩ) | Q _g (nC) |
|----------------|---------------------|-----------------------|-----------------------------|--------------------------|---------------------|
| SiHG22N60S-E3* | 600 | 20 | 22 | 190 | 115 |
| SiHG47N60S-E3* | 600 | 20 | 47 | 70 | 216 |

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WORLDWIDE SALES CONTACTS

THE AMERICAS

UNITED STATES

VISHAY AMERICAS
ONE GREENWICH PLACE
SHELTON, CT 06484
UNITED STATES
PH: +1-402-563-6866
FAX: +1-402-563-6296

ASIA

SINGAPORE

VISHAY INTERTECHNOLOGY ASIA PTE LTD.
37A TAMPINES STREET 92 #07-00
SINGAPORE 528886
PH: +65-6788-6668
FAX: +65-6788-0988

P.R. CHINA

VISHAY CHINA CO., LTD.
15D, SUN TONG INFOPORT PLAZA
55 HUAI HAI WEST ROAD
SHANGHAI 200030
P.R. CHINA
PH: +86-21-5258 5000
FAX: +86-21-5258 7979

JAPAN

VISHAY JAPAN CO., LTD.
SHIBUYA PRESTIGE BLDG. 4F
3-12-22, SHIBUYA
SHIBUYA-KU
TOKYO 150-0002
JAPAN
PH: +81-3-5466-7150
FAX: +81-3-5466-7160

EUROPE

GERMANY

VISHAY ELECTRONIC GMBH
GEHEIMRAT-ROSENTHAL-STR. 100
95100 SELB
GERMANY
PH: +49-9287-71-0
FAX: +49-9287-70435

FRANCE

VISHAY S.A.
199, BLVD DE LA MADELEINE
06003 NICE, CEDEX 1
FRANCE
PH: +33-4-9337-2727
FAX: +33-4-9337-2726

UNITED KINGDOM

VISHAY LTD.
SUITE 6C, TOWER HOUSE
ST. CATHERINE'S COURT
SUNDERLAND ENTERPRISE PARK
SUNDERLAND SR5 3XJ
UNITED KINGDOM
PH: +44-191-516-8584
FAX: +44-191-549-9556

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